# 4-Bit Magnitude Comparator

The MC14585B 4–Bit Magnitude Comparator is constructed with complementary MOS (CMOS) enhancement mode devices. The circuit has eight comparing inputs (A3, B3, A2, B2, A1, B1, A0, B0), three cascading inputs (A < B, A = B, and A > B), and three outputs (A < B, A = B, and A > B). This device compares two 4–bit words (A and B) and determines whether they are "less than", "equal to", or "greater than" by a high level on the appropriate output. For words greater than 4–bits, units can be cascaded by connecting outputs (A > B), (A < B), and (A = B) to the corresponding inputs of the next significant comparator. Inputs (A < B), (A = B), and (A > B) on the least significant (first) comparator are connected to a low, a high, and a low, respectively.

Applications include logic in CPU's, correction and/or detection of instrumentation conditions, comparator in testers, converters, and controls.

- Diode Protection on All Inputs
- Expandable
- Applicable to Binary or 8421–BCD Code
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low–power TTL Loads or One Low–power Schottky TTL Load over the Rated Temperature Range
- Can be Cascaded See Fig. 3

#### MAXIMUM RATINGS (Voltages Referenced to V<sub>SS</sub>) (Note 2.)

Symbol	Parameter	Value	Unit
$V_{DD}$	DC Supply Voltage Range	-0.5 to +18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage Range (DC or Transient)	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient) per Pin	±10	mA
P <sub>D</sub>	Power Dissipation, per Package (Note 3.)	500	mW
T <sub>A</sub>	Ambient Temperature Range	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

- Maximum Ratings are those values beyond which damage to the device may occur.
- 3. Temperature Derating:

  Plastic "P and D/DW" Packages: 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.

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# MARKING DIAGRAMS



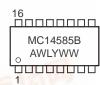
PDIP-16 P SUFFIX CASE 648 MC14585BCP AWLYYWW



SOIC-16 D SUFFIX CASE 751B 16 14585B • AWLYWW



SOEIAJ-16 F SUFFIX CASE 966



A = Assembly Location

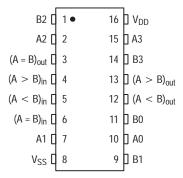
WL or L = Wafer Lot YY or Y = Year WW or W = Work Week

#### ORDERING INFORMATION

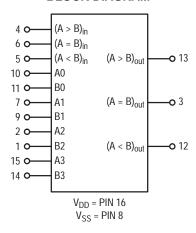
Device	Package	Shipping
MC14585BCP	PDIP-16	2000/Box
MC14585BD	SOIC-16	48/Rail
MC14585BDR2	SOIC-16	2500/Tape & Reel
MC14585BF	SOEIAJ-16	See Note 1.

 For ordering information on the EIAJ version of the SOIC packages, please contact your local ON Semiconductor representative.

# **PIN ASSIGNMENT**



#### **BLOCK DIAGRAM**



# **TRUTH TABLE** (x = Don't Care)

Inputs									
Comparing					ascadin	g		Outputs	
A3, B3	A2, B2	A1, B1	A0, B0	A < B	A = B	A > B	A < B	A = B	A > B
A3 > B3	Х	Х	Х	Х	Х	Х	0	0	1
A3 = B3	A2 > B2	Х	Х	х	х	х	0	0	1
A3 = B3	A2 = B2	A1 > B1	Х	х	Х	х	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 > B0	х	х	х	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 = B0	0	0	Х	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 = B0	0	1	х	0	1	0
A3 = B3	A2 = B2	A1 = B1	A0 = B0	1	0	х	1	0	0
A3 = B3	A2 = B2	A1 = B1	A0 = B0	1	1	х	1	1	0
A3 = B3	A2 = B2	A1 = B1	A0 < B0	Х	Х	Х	1	0	0
A3 = B3	A2 = B2	A1 < B1	Х	х	х	х	1	0	0
A3 = B3	A2 < B2	х	х	х	х	х	1	0	0
A3 < B3	Х	Х	Х	х	Х	х	1	0	0

# **ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

			V <sub>DD</sub>	- 5	5°C		25°C		125	5°C	
Characteristic		Symbol	Vdc	Min	Max	Min	Typ <sup>(4.)</sup>	Max	Min	Max	Unit
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	"0" Level	V <sub>OL</sub>	5.0 10 15	_ _ _	0.05 0.05 0.05	_ _ _	0 0 0	0.05 0.05 0.05	_ _ _	0.05 0.05 0.05	Vdc
$V_{in} = 0$ or $V_{DD}$	"1" Level	V <sub>OH</sub>	5.0 10 15	4.95 9.95 14.95	_ _ _	4.95 9.95 14.95	5.0 10 15	_ _ _	4.95 9.95 14.95	_ _ _	Vdc
Input Voltage (V <sub>O</sub> = 4.5 or 0.5 Vdc) (V <sub>O</sub> = 9.0 or 1.0 Vdc) (V <sub>O</sub> = 13.5 or 1.5 Vdc)	"0" Level	V <sub>IL</sub>	5.0 10 15	_ _ _	1.5 3.0 4.0	_ _ _	2.25 4.50 6.75	1.5 3.0 4.0	_ _ _	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V <sub>IH</sub>	5.0 10 15	3.5 7.0 11	_	3.5 7.0 11	2.75 5.50 8.25		3.5 7.0 11	_ _ _	Vdc
Output Drive Current $(V_{OH} = 2.5 \text{ Vdc})$ $(V_{OH} = 4.6 \text{ Vdc})$ $(V_{OH} = 9.5 \text{ Vdc})$ $(V_{OH} = 13.5 \text{ Vdc})$	Source	I <sub>OH</sub>	5.0 5.0 10 15	- 3.0 - 0.64 - 1.6 - 4.2	_ _ _ _	- 2.4 - 0.51 - 1.3 - 3.4	- 4.2 - 0.88 - 2.25 - 8.8	_ _ _ _	- 1.7 - 0.36 - 0.9 - 2.4	_ _ _ _	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2	_ _ _	0.51 1.3 3.4	0.88 2.25 8.8	_ _ _	0.36 0.9 2.4	_ _ _	mAdc
Input Current		I <sub>in</sub>	15	_	±0.1	_	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	_	_	_	_	5.0	7.5	_	_	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15	_ _ _	5.0 10 20		0.005 0.010 0.015	5.0 10 20	_ _ _	150 300 600	μAdc
Total Supply Current <sup>(5.)</sup> (6 (Dynamic plus Quiesce Per Package) (C <sub>L</sub> = 50 pF on all outp buffers switching)	ent,	I <sub>T</sub>	5.0 10 15			$I_T = (1$	).6 μΑ/kHz) f 1.2 μΑ/kHz) f 1.8 μΑ/kHz) f	+ I <sub>DD</sub>			μAdc

<sup>4.</sup> Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
5. The formulas given are for the typical characteristics only at 25°C.
6. To calculate total supply current at loads other than 50 pF:

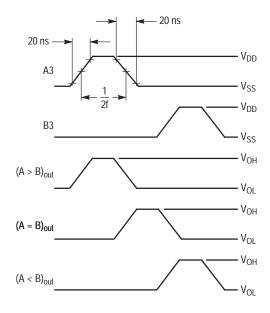
$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where:  $I_T$  is in  $\mu A$  (per package),  $C_L$  in pF,  $V = (V_{DD} - V_{SS})$  in volts, f in kHz is input frequency, and k = 0.001.

# SWITCHING CHARACTERISTICS (7.) $(C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C})$

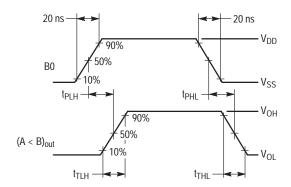
Characteristic	Symbol	V <sub>DD</sub>	Min	Typ <sup>(8.)</sup>	Max	Unit
Output Rise and Fall Time $ \begin{aligned} t_{TLH},  t_{THL} &= (1.5 \text{ ns/pF})  \text{C}_{\text{L}} + 25 \text{ ns} \\ t_{TLH},  t_{THL} &= (0.75 \text{ ns/pF})  \text{C}_{\text{L}} + 12.5 \text{ ns} \\ t_{TLH},  t_{THL} &= (0.55 \text{ ns/pF})  \text{C}_{\text{L}} + 9.5 \text{ ns} \end{aligned} $	t <sub>TLH</sub> , t <sub>THL</sub>	5.0 10 15	_ _ _	100 50 40	200 100 80	ns
Turn–On, Turn–Off Delay Time $t_{PLH}, t_{PHL} = (1.7 \text{ ns/pF}) C_L + 345 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.66 \text{ ns/pF}) C_L + 147 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.5 \text{ ns/pF}) C_L + 105 \text{ ns}$	t <sub>PLH</sub> , t <sub>PHL</sub>	5.0 10 15	_ _ _	430 180 130	860 360 260	ns

- 7. The formulas given are for the typical characteristics only at  $25\,^{\circ}$ C.
- 8. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.



Inputs (A>B) and (A=B) high, and inputs B2, A2, B1, A1, B0, A0 and (A<B) low. f in respect to a system clock.

Figure 1. Dynamic Power Dissipation Signal Waveforms



Inputs (A>B) and (A=B) high, and inputs B3, A3, B2, A2, B1, A1, A0, and (A<B) low.

Figure 2. Dynamic Signal Waveforms

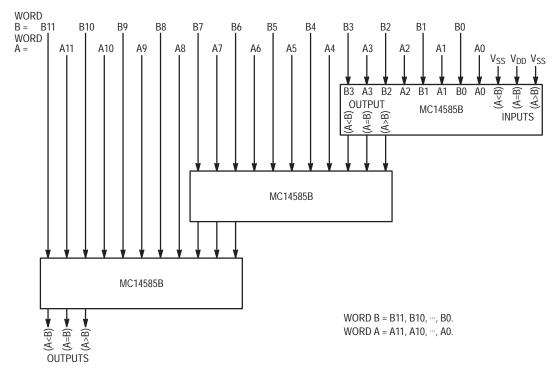
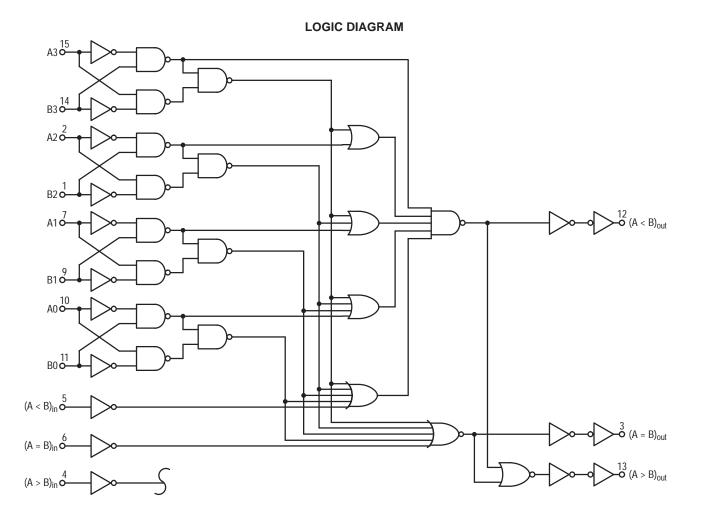
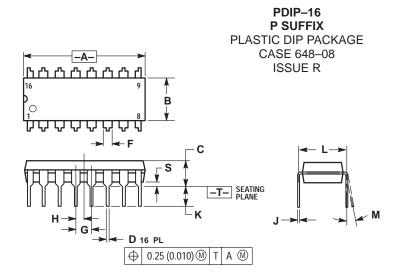


Figure 3. Cascading Comparators



#### PACKAGE DIMENSIONS



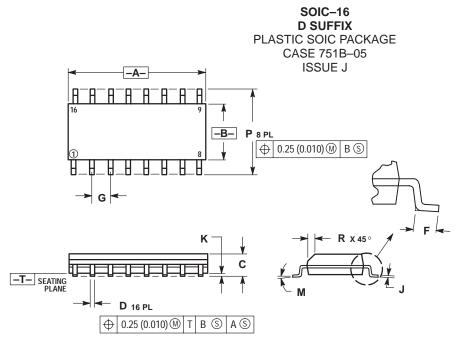
- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100	BSC	2.54 BSC		
Н	0.050	BSC	1.27 BSC		
٦	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
M	0°	10 °	0 °	10 °	
S	0.020	0.040	0.51	1.01	



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.

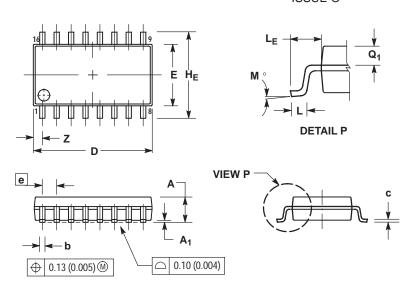
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL
  IN EXCESS OF THE D DIMENSION AT
  MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	) BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

#### PACKAGE DIMENSIONS

#### SOEIAJ-16 **F SUFFIX** PLASTIC EIAJ SOIC PACKAGE CASE 966-01 **ISSUE O**



#### NOTES:

- OTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.00A) PER SIDE
- OR PROTRUSIONS SHALL NOT EXCEED 0.15
  (0.006) PER SIDE.
  4. TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.
  5. THE LEAD WIDTH DIMENSION (b) DOES NOT
  INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
  TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION.
  DAMBAR CANNOT BE LOCATED ON THE LOWER
  RADIUS OR THE FOOT. MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD
  TO BE 0.46 (0.018).

10 02 0110 ( 01010)1								
	MILLIN	METERS	INC	HES				
DIM	MIN	MAX	MIN	MAX				
Α		2.05		0.081				
A <sub>1</sub>	0.05	0.20	0.002	0.008				
b	0.35	0.50	0.014	0.020				
С	0.18	0.27	0.007	0.011				
D	9.90	10.50	0.390	0.413				
Ε	5.10	5.45	0.201	0.215				
е	1.27	BSC	0.050	BSC				
HE	7.40	8.20	0.291	0.323				
L	0.50	0.85	0.020	0.033				
LE	1.10	1.50	0.043	0.059				
M	0 °	10 °	0 °	10°				
Q <sub>1</sub>	0.70	0.90	0.028	0.035				
Z		0.78		0.031				

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